Ordering number:ENN6406

N-Channel Silicon MOSFET

2SK2530

Ultrahigh-Speed Switching Applications

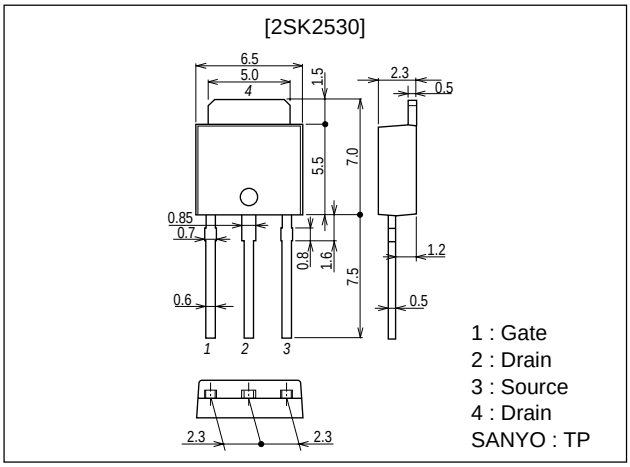
Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- Low voltage drive.

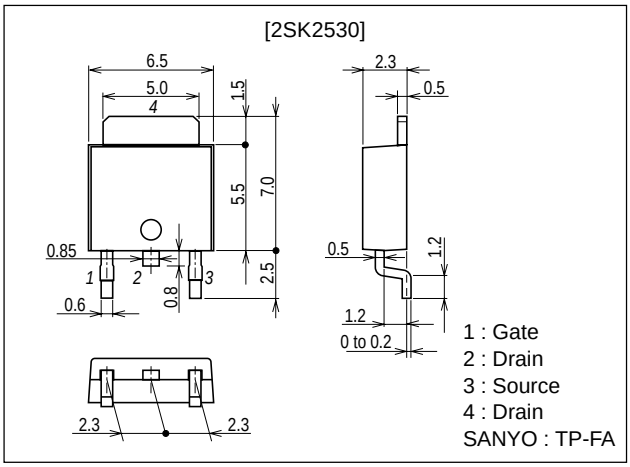
Package Dimensions

unit:mm

2083B



2092B



SANYO Electric Co.,Ltd. Semiconductor Company

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Specifications

Absolute Maximum Ratings at Ta = 25˚C

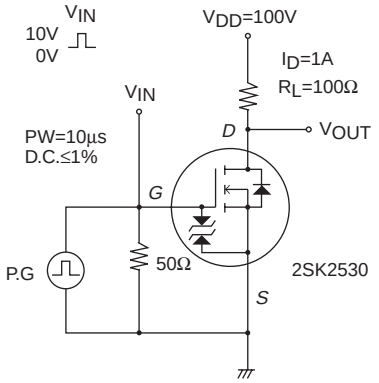
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		250	V
Gate-to-Source Voltage	V_{GSS}		±30	V
Drain Current (DC)	I_D		2	A
Drain Current (Pulse)	I_{DP}	PW≤10µs, duty cycle≤1%	8	A
Allowable Power Dissipation	P_D		1	W
		Tc=25˚C	20	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

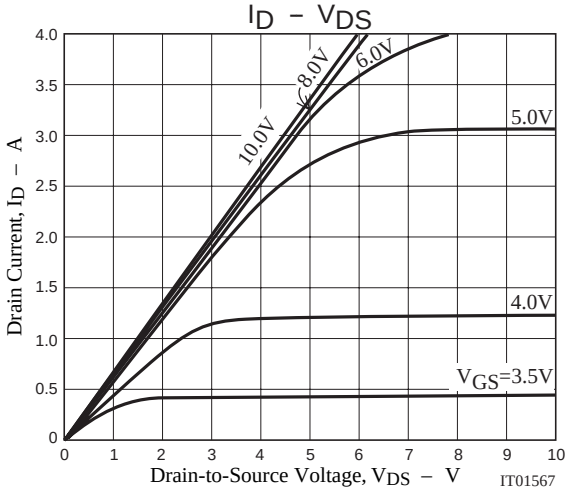
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	250			V
Gate-to-Source Breakdown Voltage	$V_{(BR)GSS}$	I_G=±100µA, V_{GS}=0	±30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=250V, V_{GS}=0			1.0	mA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±25V, V_{DS}=0			±10	µA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, I_D=1mA	2.0		3.0	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=1A	1.3	1.9		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=1A		1.5	2.0	Ω
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		160		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		40		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		15		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit		10		ns
Rise Time	t_r	See specified Test Circuit		13		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit		80		ns
Fall Time	t_f	See specified Test Circuit		30		ns
Diode Forward Voltage	V_{SD}	I_S=2A, V_{GS}=0		1.0	1.5	V
Diode Reverse Recovery Time	t_{rr}	I_S=2A, di / dt=100µA/µs		90		ns

Marking : K2530

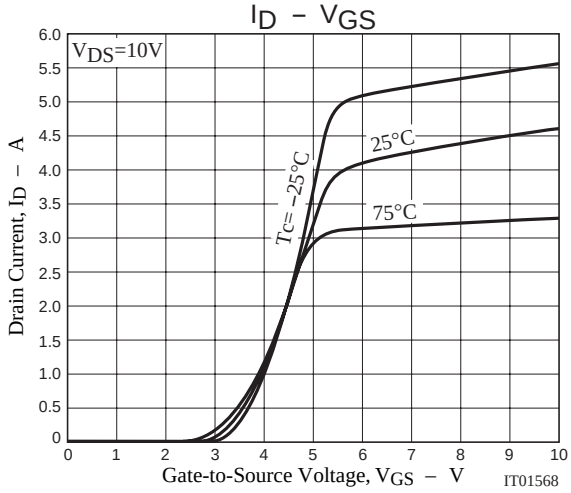
Switching Time Test Circuit



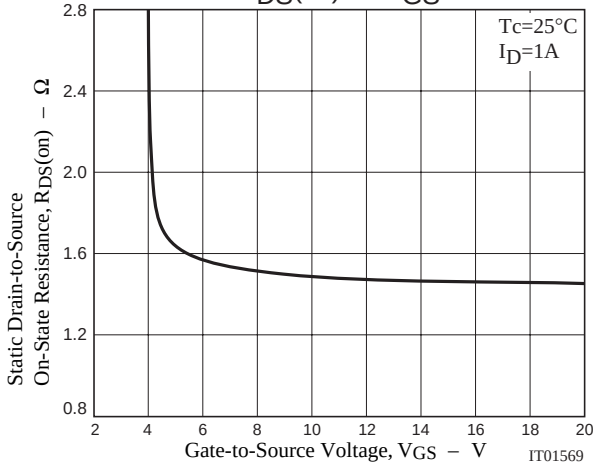
I_D – V_{DS}



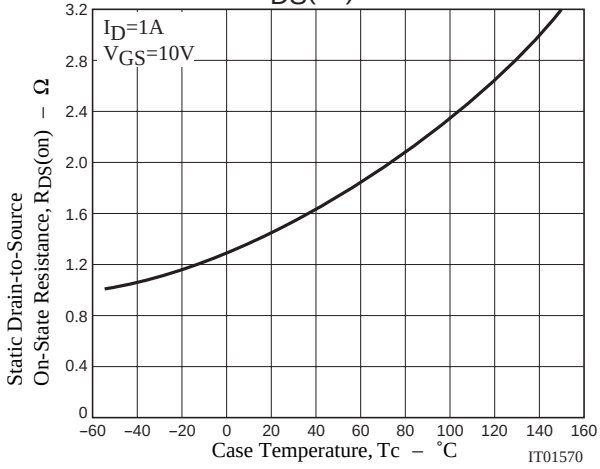
I_D – V_{GS}



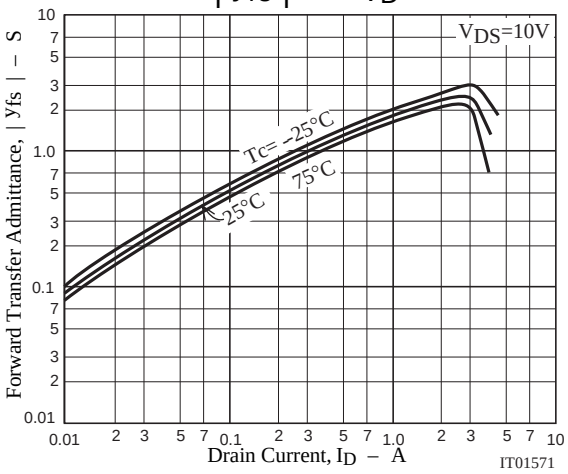
$R_{DS}(on)$ – V_{GS}



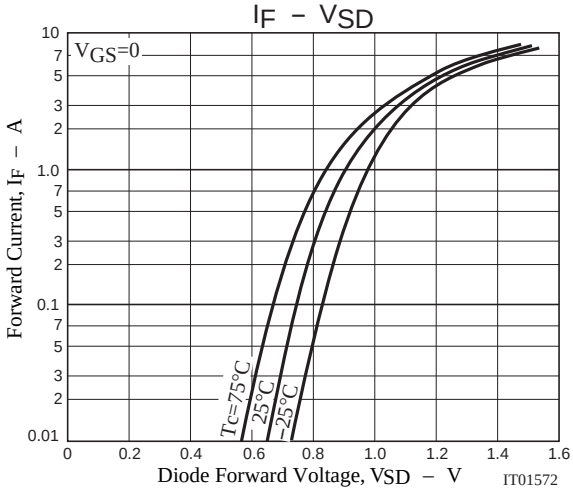
$R_{DS}(on)$ – Tc



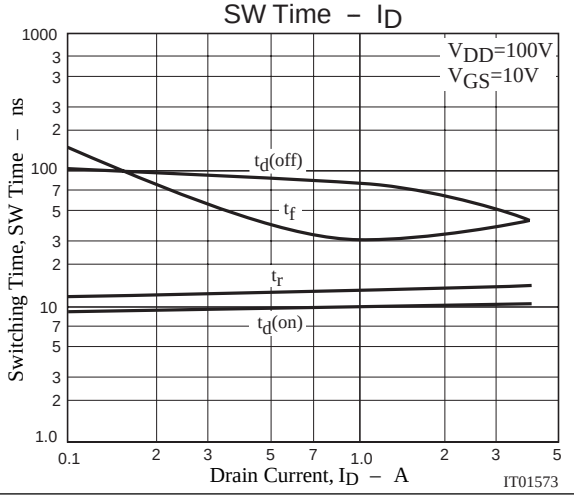
$|y_{fs}|$ – I_D



I_F – V_{SD}



SW Time – I_D



Ciss, Coss, Crss – V_{DS}